

IN THE SPECIFICATION:

Please amend the specification as follows:

Page 1, lines 1-5 (the first paragraph on page 1): please replace this paragraph with the following rewritten paragraph:

A1
This application is related to U.S. Patent Application No. _____ (Attorney Docket No. LAM2P256) No. 6,541,361, filed on the same day as the instant application and entitled "PLASMA ENHANCED METHOD FOR INCREASING SILICON-CONTAINING PHOTORESIST SELECTIVITY." This application is hereby incorporated by reference.

Page 7, line 8 (the brief description for Figure 2): please replace this paragraph with the following rewritten paragraph:

A2
Figure 2 illustrate illustrates a block diagram depicting a developed substrate.

Page 12, lines 7-14 (the first full paragraph on page 12): please replace this paragraph with the following rewritten paragraph:

A3
In a preferred embodiment of the invention as illustrated in Figure 5 3, the top layer 110 of silicon-containing photoresist has a thickness of about 2000 Å while the bottom layer 116 of non silicon-containing photoresist has a thickness of about 6000 Å. In a general embodiment, the silicon-containing photoresist has a thickness that ranges between 1000 Å and about 3000 Å, while the bottom layer 116 of non silicon-containing photoresist has a thickness that ranges between about 3000 Å and about 8000 Å. In

A3
CONT.

another embodiment of the invention, the cross-linked layer 138 has a thickness between about 5% to about 75% of the thickness of the original layer 110.
